

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Original) A low dielectric constant film comprising a film comprising at least fine diamond particles and pores, wherein said low dielectric constant film comprises at least one metal selected from the group of metals whose carbonate salt or a sulfate salt has a solubility of 1 g/100 g or less at an ambient temperature.

2. (Original) The low dielectric constant film of claim 1, wherein said metal is at least one member of the group consisting of calcium, strontium, barium, mercury, silver, lead and radium.

3. (Original) A low dielectric constant film having at least fine diamond particles and pores, wherein said low dielectric constant film is treated with an aqueous solution of a salt of at least one metal selected from the group of metals whose carbonate salt or sulfate salt has a solubility of 1 g/100 g or less at an ambient temperature.

4. (Original) The low dielectric constant film of claim 3, which is treated with an aqueous solution of a salt of at least one metal of the group consisting of calcium, strontium, barium, mercury, silver, lead and radium.

5. (Currently Amended) An electronic part comprising a low dielectric constant film according to ~~any one of claims 1 to 4~~ claim 1 as at least one constituent element.

6. (Original) A low dielectric constant film comprising a film comprising at least fine diamond particles and pores, wherein the surface of said fine diamond particles has a group of a general formula of -X group which is more hydrophobic than hydroxyl group instead of hydroxyl group.

7. (Currently Amended) The low dielectric constant film of ~~claim 1~~ claim 6, wherein X in said general formula of -X group is at least one member selected from the group consisting of hydrogen, fluorine, C₁ to C₄ alkoxy group, phenoxy group, o-(m- or p-)alkylphenoxy group (in which alkyl group is C₁ to C₄ alkyl group), OCOR, OCONRR', OSiR₃ [in which R and R' each represents hydrogen, C₁ to C₄ alkyl group, phenyl group or o-(m- or p-)alkylphenyl group].

8. (Currently Amended) The low dielectric constant film of ~~claim 1 or 2~~ claim 6, wherein X in the general formula of -X group is OSiR₃ (where R is C₁ to C₄ alkyl group).

9. (Currently Amended) An electronic part containing said dielectric constant film of ~~any one of claims 1 to 3~~ claim 6 as at least one constituent element.

10. (Original) A method of manufacturing a low dielectric constant film, said method comprising the step of reacting active hydroxyl groups on the surface of fine diamond particles and a hydrophobic agent.

11. (Currently Amended) The method of manufacturing a low dielectric constant film of ~~claim 5~~ claim 10, wherein said hydrophobic agent is at least one member selected

from the group consisting of hexaalkyl disilazane, trialkyl monohalogen silane, triphenyl monohalogen silane, arylated alkyl monohalogen silane, dialkyl dihalogen silane, trialkyl monomethoxy silane, triphenyl monomethoxy silane, arylated monoalkoxy alkyl silane, dialkyl dimethoxy silane and diazoalkylene.

12. (Original) A low dielectric constant film comprising a film comprising at least fine diamond particles and pores, wherein the surface of said fine diamond particles is treated with at least one single substance of the following (a) or a mixture of substances of at least one of (a) and at least one of (b) as described below:

(a) a substance represented by the general formula:



(b) a substance represented by the general formula;



(where $n = 1$ or 2 , $m =$ an integer of 0 to 3 , X represents a halogen group, C_1 to C_6 alkoxy group or phenoxy group, and R represents C_1 to C_6 alkyl group).

13. (Currently Amended) The low dielectric constant film of ~~claim 1~~ claim 12, wherein X is at least one member selected from the group consisting of chlorine group, methoxy group and ethoxy group and R represents methyl group or ethyl group in the general formula (a) and the general formula (b).

14. (Currently Amended) The low dielectric constant film of ~~claim 1 or 2~~ claim 12, wherein m is 1 in the general formula (a) and the general formula (b).

15. (Currently Amended) The low dielectric constant film of ~~any one of claims 1 to 3~~ claim 12, wherein n is 1 in the general formula (a).

16. (Currently Amended) The low dielectric constant film of ~~claim 1,~~ claim 12, wherein said substance of the general formula (a) is at least one member selected from the group consisting of dichloro tetramethyl disiloxane, dimethoxy tetramethyl disiloxane, tetrachloro dimethyl disiloxane and tetramethoxy dimethyl disiloxane, and said substance of the general formula (b) is at least one member selected from the group consisting of hexachlorodisiloxane, hexamethoxy disiloxane and hexaethoxy disiloxane.

17. (Currently Amended) A- The low dielectric constant film of claim 12 ~~comprising a film comprising at least fine diamond particles and pores~~, wherein the surface of said fine diamond particles is treated with at least one member of the general formula (b) in which X represents a C₁ to C₆ alkoxy group or phenoxy group.

18. (Currently Amended) An electronic part comprising the low dielectric constant film of ~~any one of claims 1 to 6~~ claim 12 as at least one constituent element.

19. (Currently Amended) A method of manufacturing a low dielectric constant film of claim 12, said method comprising the step of chemically reacting hydroxyl groups on the

surface of fine diamond particles and at least one single substance of (a) or a mixed substances of at least one of (a) and at least one of (b) described above.

20. (Currently Amended) The method of manufacturing a low dielectric constant film of ~~claim 8~~ claim 19, wherein said substance of the general formula (a) is at least one member selected from the group consisting of dichloro tetramethyl disiloxane, dimethoxy tetramethyl disiloxane, tetrachloro dimethyl disiloxane and tetramethoxy dimethyl disiloxane, and therein said substance of the general formula (b) is at least one member selected from the group consisting of hexachlordisiloxane, hexamethoxy disiloxane and hexaethoxy disiloxane.